



## SIHG14N50D-E3 Information



For Reference Only

Part Number SIHG14N50D-E3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 14A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## SIHG14N50D-E3 Specifications

Manufacturer Part Number         SIHG14N50D-E3           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         14A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         58nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1144pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         208W (Tc)           Rds On (Max) @ Id, Vgs         400 mOhm @ 7A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247AC           Package / Case         TO-247AC		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-247-3  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Torin to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  14A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1144pF @ 100V  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  A00 mOhm @ 7A, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-247AC  Package / Case	Manufacturer Part Number	SIHG14N50D-E3
Package         TO-247-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         14A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         58nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1144pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         208W (Tc)           Rds On (Max) @ Id, Vgs         400 mOhm @ 7A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247AC           Package / Case         TO-247-3	Manufacturer	Vishay Siliconix
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1144pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)208W (Tc)Rds On (Max) @ Id, Vgs400 mOhm @ 7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247AC		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1144pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)208W (Tc)Rds On (Max) @ Id, Vgs400 mOhm @ 7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sv @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package TO-247AC Package / Case TO-247-3	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1144pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)208W (Tc)Rds On (Max) @ Id, Vgs400 mOhm @ 7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Automatical Supplier Device Package  Package / Case  14A (Tc)  16V  250μA  58NC @ 10V  1144pF @ 100V  20V  40V  40V  40V  40V  40V  40V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 7A, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-247-AC  TO-247-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-AC  Package / Case  TO-247-3	Current - Continuous Drain (Id) @ 25°C	14A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1144pF @ 100V  Vgs (Max)  ±30V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 7A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247AC  Package / Case  TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-AC  Package / Case  TO-247-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)208W (Tc)Rds On (Max) @ Id, Vgs400 mOhm @ 7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	58nC @ 10V
FET Feature - Common Power Dissipation (Max) 208W (Tc) Rds On (Max) @ Id, Vgs 400 mOhm @ 7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	1144pF @ 100V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 7A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247AC  Package / Case  TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs400 mOhm @ 7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247AC  Package / Case  TO-247-3	Power Dissipation (Max)	208W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	400 mOhm @ 7A, 10V
Supplier Device Package TO-247AC Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247AC
Report errors?	Package / Case	TO-247-3
		Report errors?

#### SIHG14N50D-E3 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### SIHG14N50D-E3 Payment Methods





















### SIHG14N50D-E3 Shipping Methods













If you have any question about SIHG14N50D-E3, please do not hesitate to contact us!

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